



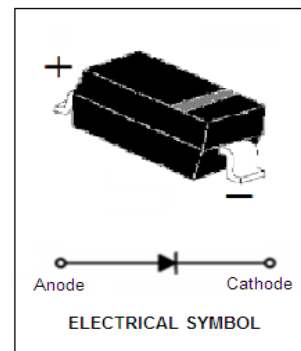
SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes

BAV19W/BAV20W/BAV21W (FAST SWITCHING DIODES)

特点/Features :

- Fasting Switching Speed ;
- Surface Mount Package Ideally Suited for Automatic Insertion ;
- For General Purpose Switching Applications;
- High Conductance;



印章/ Marking:

- BAV19W: A8**
- BAV20W: T2**
- BAV21W: T3**

极限参数/Absolute maximum ratings(Ta=25°C)

参数	符号	BAV19W	BAV20W	BAV21W	单位
Non-Repetitive Peak Reverse Voltage	V_{RM}	120	200	250	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	100	150	250	V
Working Peak Reverse Voltage	V_{RWM}	100	150	250	V
DC Blocking Voltage	V_R	100	150	250	V
RMS Reverse Voltage	$V_{R(RMS)}$	71	106	141	V
Forward Continuous Current	I_{FM}	400			mA
Average Rectified Output Current	I_O	200			mA
Peak Forward Surge Current	I_{FSM}	2.5 (@=1.0mS) 0.5 (@=1.0S)			A
Repetitive Peak Forward Current	I_{FRM}	625			mA
Power Dissipation	P_D	0.5			W
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	250			°C/W
Storage Temperature	T_{stg}	-55~150			°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最大值	单位
正向电压/Forward Voltage	V_{F1}	$I_F=100mA$	1.0	V
	V_{F2}	$I_F=200mA$	1.25	V
反向漏电流/Reverse Current BAV19W BAV20W BAV21W	I_R	$V_R=100V$	0.1	μA
		$V_R=150V$	0.1	μA
		$V_R=200V$	0.1	μA
端电容/Capacitance Between Terminals	C_T	$V_R=0, f=1MHz$	5	pF
反向恢复时间/Reverse Recovery Time	t_{rr}	$I_F=I_R=30mA,$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$	50	nS